PORTIONS OF THIS DOCUMENT

ARE
ILLEGIBLE

BLANK PAGE

LA-UR -7:-1871

MASTER

TITLE: INTERVALENCE BAND ABSORPTION IN ELECTRON HOLE DROPLETS

AUTHOR(S): R. N. Silver and C. H. Aldrich

SUBMITTED TO:

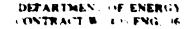
14th International Conference on the Physics of Semiconductors, Edinburgh, Scotland, September 4 - 8, 1978.

the acceptance of the article the publishes reinguises the the U.S. Concernment retains a noncuclosed to alth free between to publish or reprotate the published form of this contribution, or to all a others to the up for U.S. Concernment

The Lorin United Separatific Laboratory requests that the publisher edentify this process as work performed under the appropriate of the Department of Energy

los diamos
scientific laboratory
of the University of California
101 ALANOS HIM PIECO 1-545

An Affirmative Action town Opposite to prepar



INTERVALENCE BAND ABSORPTION IN ELECTRON HOLE DROPLETS

by

R. N. Silver
Theoretical Division, Los Alamos Scientific Laboratory
University of California
Los Alamos, New Mexico 87545

and

C. H. Aldrich
N-Division, Los Alamos Scientific Laboratory
University of California
Los Alamos, New Mexico 67545

ABSTRACT

The broad absorption lineshape observed for transitions between the heavy hole and spin orbit split bands in EHD in Ge is explained. It is due to the momentum spreading of the hole wave function as calculated by multiple scattering theory.

R N Silver, C H Aldrich MS 457 Los Alamos Scientific Laboratory Los Alamos, New Mexico 87545

The broad absorption lineshape observed for transitions between the heavy hole and spin orbit split bands in EHD in Ge is explained. It is due to the nomentum spreading of the hole wave function as calculated by multiple scattering theory.

Pokrovsky et. al. have observed a broad absorption due to transitions between the heavy hole and spin orbit split bands in Ge. It is much wider than predicted by the free particle theory which has successfully explained the lineshape for IHD luminescence. Similarly wide absorption is also observed for holes bound into excitons or to acceptors. In the latter case, Smith et. al. have explained the lineshape in terms of the momentum spreading of the hole bound state wave function. In IHD or in degenerately doped semiconductors the screening is sufficiently large that bound states are absent. So present the first explanation of the lineships in these systems.

In a simplified model where the potential acts only on holes in a spherical heavy tole bant, the absorption is

$$\sigma(hv) \sim \sum_{i} f(\epsilon_{i}) \int d^{3}k |k|^{2} |M|^{2} |\langle k|\psi_{i}\rangle|^{2} \delta(hv - \epsilon_{k}^{50} + \epsilon_{i}) = 1$$

where the the acceptor or exciten wave functions in the bound state case, and become plane wave states kerin the free hole theory. A comparison of the free hole theory including the effect of mass anisotropy with experiment is shown as the dashed line if Fig. 1. Intervalence hand transitions conserve momentum (direct transition) and the occupied states in the heavy hole hand are restricted to momenta less than the Fermi momentum. Thus, a sharp cutoff is predicted in the free hole theory for energies about 25 mey above the threshold for the transition. This conclusion is not altered by the inclusion of some many body offects such as final state interactions or renormalization

of the hole energy. We show that the momentum spreading of the hole wave function due to multiple scattering can explain the high energy tail observed experimentally.

Consider the simpler problem of the effect of impurity scattering on the absorption. The problem then is the choice of $|\psi_i\rangle$ in (1). We propose a wave function based on the idea of a "coherent wave" in multiple scattering theory 5 . In the presence of uncorrelated scatterers a plane wave state is attenuated and the effective wave vector is shifted. This may be expressed by the addition to the energy $|\epsilon_k|$ of a plane wave state of a self energy $|\epsilon_k|$ given by $|\epsilon_k| |\epsilon_k| |\epsilon_k| |\epsilon_k|$. Here $|\epsilon_k|^5 > \epsilon_k$ denotes a scattering wave function for a single impurity, $|\epsilon_k| > \epsilon_k$ a plane wave state, and $|\epsilon_k| > \epsilon_k$ the impurity density. This is the same as the well known relation of self energy to the forward scattering amplitude. Then we propose a multiple scattering wave function

$$\langle \vec{k} | \psi_{\vec{k}}^{\dagger} \rangle = (2\pi)^{3} \delta(\vec{k} - \vec{k}') - \frac{\sum_{j} i(\vec{k} - \vec{k}') \cdot r_{j}}{\epsilon_{k} + \Sigma(\vec{k}) - \epsilon_{k}'} \langle \vec{k} | V | \psi_{\vec{k}}^{Q} \rangle$$

Note that in the limit of a single impurity \mathbb{R}^n reduces to the usual expression for the projection of a scattering state onto a plane wave state with $\mathbb{R}(k)$ becoming a \mathbb{R}^n . The sum over \mathbb{R}^n runs over all the impurities.

Now substitute (2) into (1) and average over the impurity positions. The terms which are singular as $k \in \mathbb{R}^n$ exactly cancel, with the result

$$\mathbf{e(hv)} = 2n_{1} \int \frac{d^{3}k^{*}}{(2\pi)^{6}} \left((\varepsilon_{k}^{*}) \right) \int \frac{d^{3}k|k|^{2} |M|^{2} |\zeta_{k}^{k}|V| \left((\varepsilon_{k}^{*})^{2} + (Im\Sigma(k))^{2} + (Im\Sigma(k))^{2} \right)}{\left((\varepsilon_{k}^{*} - \varepsilon_{k}^{*}) + Rc \Sigma(k) \right)^{2} + (Im\Sigma(k))^{2}}$$
(5)

This expression contains the effect of the momentum spreading of the hole wave function which is responsible for the lineshape in the bound state case. It also contains the broadening of plane wave states due to multiple scattering. One may prove with the aid of the optical theorem that in

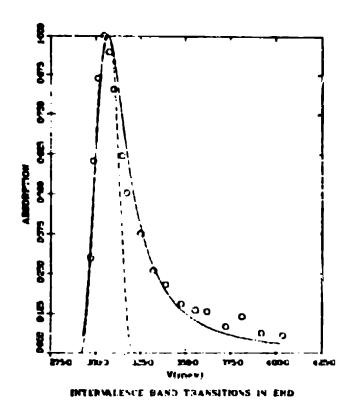


Fig 1. Data points are from Pokrovsky et. al. Dashed line is the free hole theory. Solid line is the present multiple scattering theory.

the limit of no scattering (3) goes to the free hole theory.

These ideas may be generalized to electron hole droplets by replacing impurity scattering by electron and hole scattering. We have carried out a calculation of this kind in the Born approximation with a static Yukawa screened interaction. The fit shown as the solid line in Fig 1 was obtained with a screening momentum of about one-half the Thomas form: value. Qualitative agreement with the slowly decreasing absorption tail at high energies is obtained. Other approximations made in this calculation are (1) the conduction and valence bands are taken to be spherical with density of states masses; (ii) absorption due to the light hole band is ignored; (iii) scattering effects in the spin orbit split band and the counting between spin orbit and heavy hole bands due to the coulomb interaction are ignored; (iv) the matrix element. M. which is normally anisotropic is taken to be constant.

A calculation in which the Yukawa potential is replaced by

dynamically "screened potential such as given by the RPA is in progress. A preful comparison with the RPA will require inclusion 1 structure anisotropy, hand coup ling, and especia e effects of scattering in the spin orbit split band. ane latter is necessary to insure the proper cancellation of the plasmon contribution at zero momentum transfer. All these effects will act to broaden the absorption. Since the absorption is sensitive to the high momentum components of the wave function, it will be an important test for theories of electron correlation.

In conclusion, we have presented the first explanation of intervalence band absorption in PHD to go beyond the free hole theory. Other direct transitions such as the gain spectra of highly excited or heavily doned direct gap semiconductors also show strong deviations from the predictions of free particle theories for lineshapes 1. We expect that the same multiple scattering ideas will find application to these problems.

REFERENCES

- Pokrovsky Ya F., Svistunova K. I. 1971 Fir. Iverd. Tela 13 2788 (Soviet Physics - Solid State 15 2831 1971)
- Smith D.I., Chen M. McGill T. C. 1976 Physical Review 2.
- B14 3504-3510 Lax M 1951 Fevicus of Motern Physics 23 287 312 Gobel G 1974 Amplied Physics Letters 24 4.2 4.41 Leheny R F. Shah J 1977 Physical Review Letters 38 511-511